YJ Planar Schottky Barrier Diode Die Specification

100V 30A, 122mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB122S100AS-290A

Main Products Characterstics

- Average forward current: IF(AV) = 30 A
- Maximum operating junction temperature: Tj = 175 °C
- ESD rating: >2KV, per IEC61000-4-2 (Contact Discharge)
- Top metal: AL

Maximum Ratings

Parameter	Symbol	Rating
Repetitive peak reverse voltage	V_{RRM}	100 V
Average forward current		
		-50 to +175 °C

Static Electrical Characteristics (Ta = 25°C)

Parameter	Symbol
Reverse breakdown voltage I_R = 1mA	V_{BR}
I_F = 15A P ,se Test: tp = 300 μs, δ≤ 2%	
Maximum reverse current V_R = V_{RRM} P ,se Test: tp = 300 μs, δ≤ 2%	I_R

Device Schematics and Outline Drawing

Die Thickness *	
Die Size **	122 Mils
Top Metal Pad	
Active Area	

Top Metal

Back Metal

Note: 1 * : Also can offer device with 8 mils thickness
2 **: Cutting street width is around 1.5 mils

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

does not guarantee device performance after assembly.
All operating parameters must be validated for each customer application by customer's technical experts.

Data sheet information is subjected to change without notice.

Recommended Storage Environment:

Store in original container, in dessicated nitrogen, with no contamination.

Shelf life for parts stored in above condition is 2 years.

If the storage is done in normal atmosphere shelf life is reduced to 6 months.

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